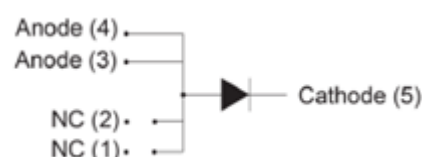


3rd Generation 650V/6A SiC Schottky Barrier Diode

Features

- Revolutionary semiconductor material - Silicon Carbide (SiC)
- No reverse recovery
- High-speed switching performance
- Temperature-independent switching behavior
- System cost / size savings due to reduced cooling requirements
- Junction temperature range from -55°C to 175°C
- RoHS compliant



Package Type: DFN 8*8-4L



Potential Applications

- Industrial power supplies: Industrial UPS
- Battery chargers
- Solar inverters
- Switch mode power supplies

Description

The SDS065J006S3 SiC Schottky Barrier Diode (SBD) has been developed using Sanan's advanced 3rd generation SiC SBD technology with the highest performance and reliability. It registers higher efficiency, higher operation temperature and lower loss and can be operated at higher frequency than Si-based solutions. As to the Schottky structure, it shows no recovery at turn-off and allows a low leakage current with reverse voltage up to 650V. It can contribute to system miniaturization and achieve lightweight system design. Using RoHS compliant components, it is qualified for use in industrial application.

Product Specifications

Device	V_{RRM}	I_F (135°C)	V_F (25°C)	Q_C	Marking
SDS065J006S3	650V	11A	1.30V	17nC	DS065006S3

CONTENTS

Features.....	1
Potential Applications.....	1
Description.....	1
Product Specifications	1
Table 1 Maximum Ratings.....	3
Table 2 Thermal Resistance.....	3
Table 3 Static Electrical Characteristics.....	4
Table 4 Dynamic Electrical Characteristics	4
Electrical Characteristic Diagrams.....	5
Package Information	7
Recommended Solder Pad Layout.....	8
Ordering Information	8
Important Notices – Read Carefully	9
Warning	9

Table 1. Maximum Ratings

(T_c = 25°C, unless otherwise specified)

Parameter	Symbol	Value	Unit	Test conditions
Repetitive peak reverse voltage	V _{RRM}	650	V	T _C = 25°C
Surge peak reverse voltage	V _{RSM}	650		T _C = 25°C
DC reverse voltage	V _{DC}	650		T _C = 25°C
Continuous forward current	I _F	23	A	T _C = 25°C
		11		T _C = 135°C
		6		T _C = 155°C
Surge non-repetitive forward current	I _{FSM}	48	A	T _C = 25°C, t _p = 10ms, half sine pulse
Non-repetitive peak forward current	I _{F,Max}	330	A	T _C = 25°C, t _p = 10μs, pulse
Surge repetitive forward current	I _{FRM}	35	A	T _C = 25°C, t _p = 10ms, half sine wave D = 0.1
Power dissipation	P _{tot}	115	W	T _C = 25°C
i ² t value	∫i ² dt	11.5	A ² s	T _C = 25°C, t _p = 10ms
Operating junction temperature	T _j	-55~175	°C	
Storage temperature	T _{stg}	-55~175	°C	

Table 2. Thermal Resistance

Parameter	Symbol	Values			Unit	Test condition
		Min.	Typ.	Max.		
Thermal resistance from junction to case	R _{th(j-c)}	/	1.3	/	°C/W	

Table 3. Static Electrical Characteristics

($T_j = 25^\circ\text{C}$, unless otherwise specified)

Parameter	Symbol	Values			Unit	Test conditions
		Min.	Typ.	Max.		
DC blocking voltage	V_{DC}	650	/	/	V	$I_R = 100\ \mu\text{A}$
Forward voltage	V_F	/	1.30	1.50	V	$I_F = 6\text{A}$, $T_j = 25^\circ\text{C}$
		/	1.55	1.80		$I_F = 6\text{A}$, $T_j = 175^\circ\text{C}$
Reverse current	I_R	/	1	18	μA	$V_R = 650\text{V}$, $T_j = 25^\circ\text{C}$
		/	2	48		$V_R = 650\text{V}$, $T_j = 175^\circ\text{C}$

Table 4. Dynamic Electrical Characteristics

($T_j = 25^\circ\text{C}$, unless otherwise specified)

Parameter	Symbol	Values			Unit	Test conditions
		Min.	Typ.	Max.		
Total capacitance	C	/	310	/	pF	$V_R = 0\text{V}$, $f = 1\text{MHz}$
		/	33	/		$V_R = 200\text{V}$, $f = 1\text{MHz}$
		/	28	/		$V_R = 400\text{V}$, $f = 1\text{MHz}$
Total capacitive charge	Q_C	/	17	/	nC	$V_R = 400\text{V}$
Capacitance stored energy	E_C	/	2.6	/	μJ	$V_R = 400\text{V}$

Electrical Characteristic Diagrams

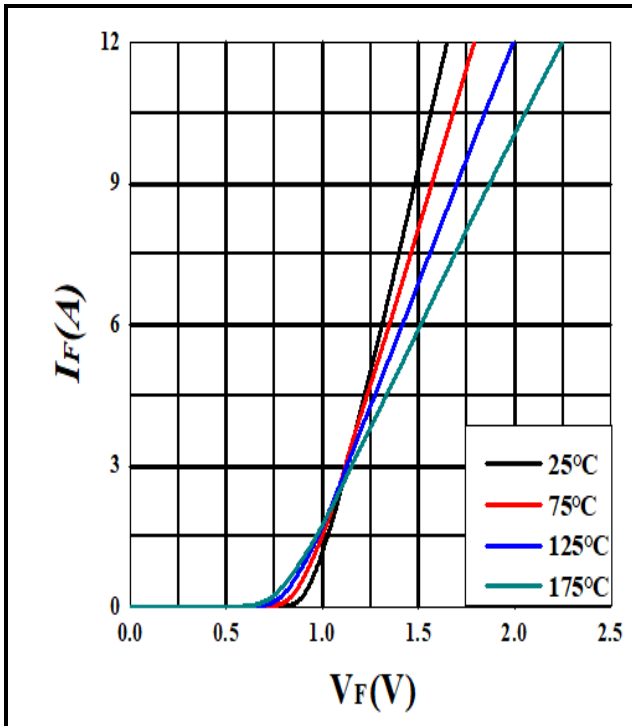


Figure 1. Forward characteristics

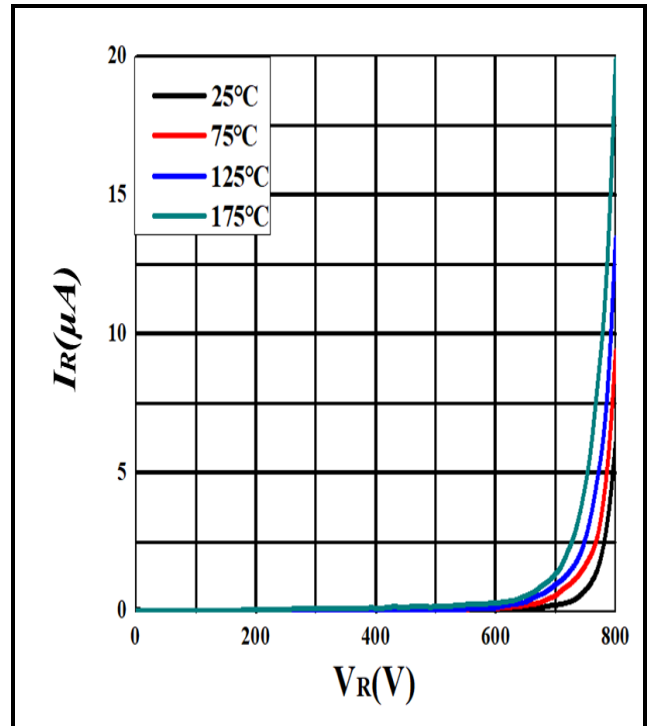


Figure 2. Reverse characteristics

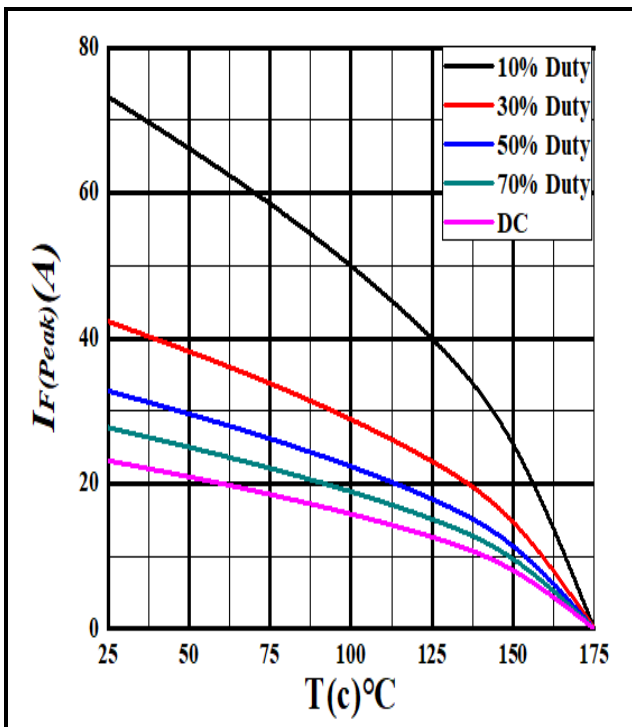


Figure 3. Current derating

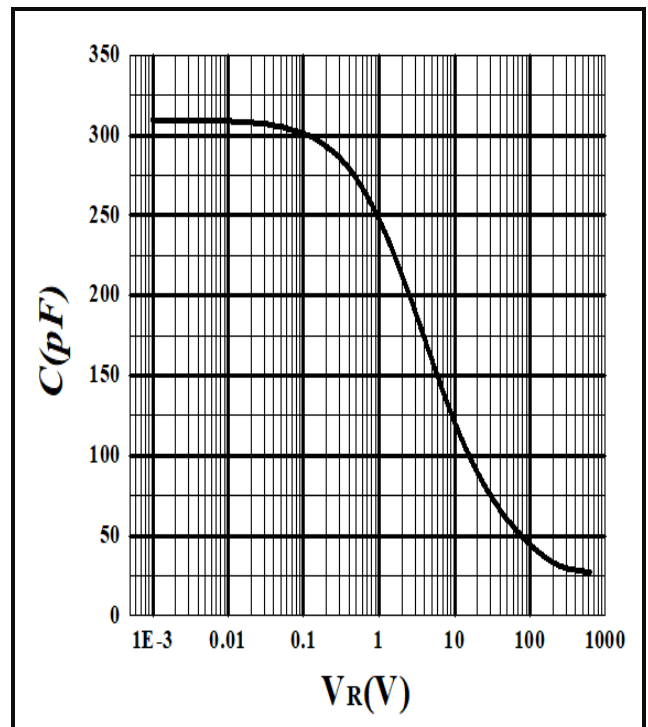


Figure 4. Capacitance vs. reverse voltage

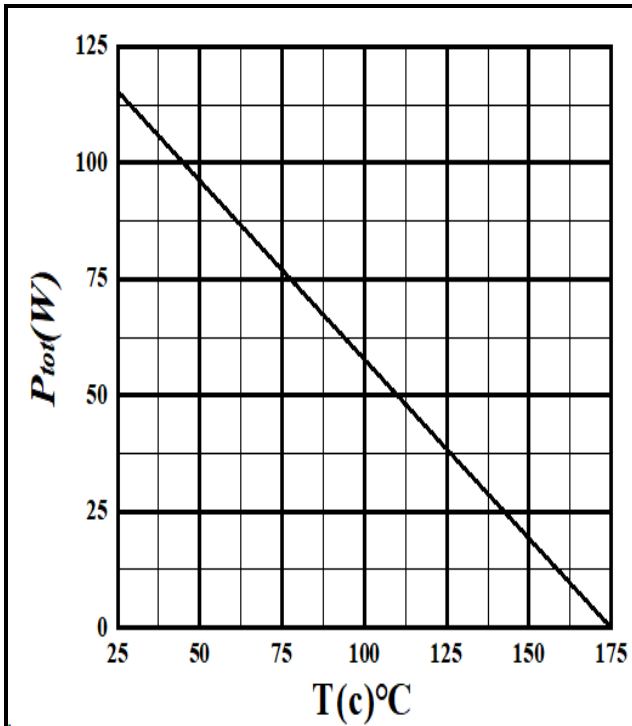


Figure 5. Power derating

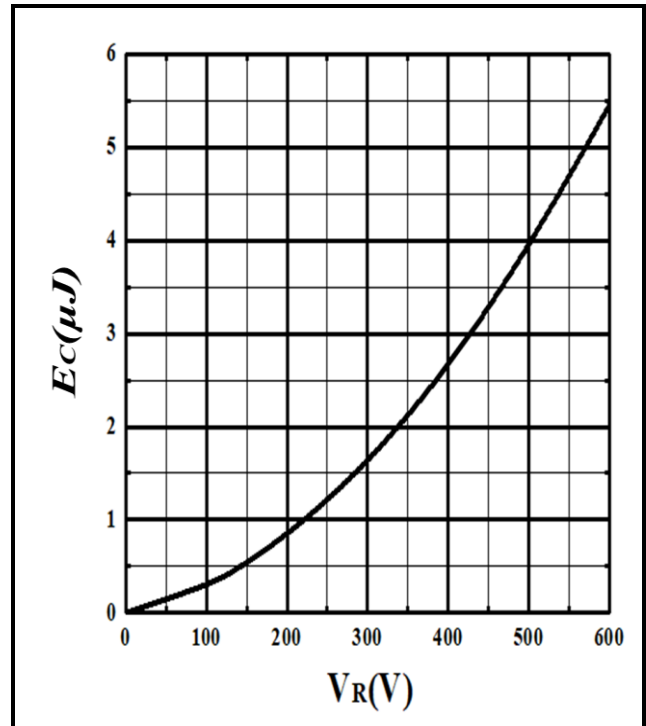


Figure 6. Capacitance stored energy

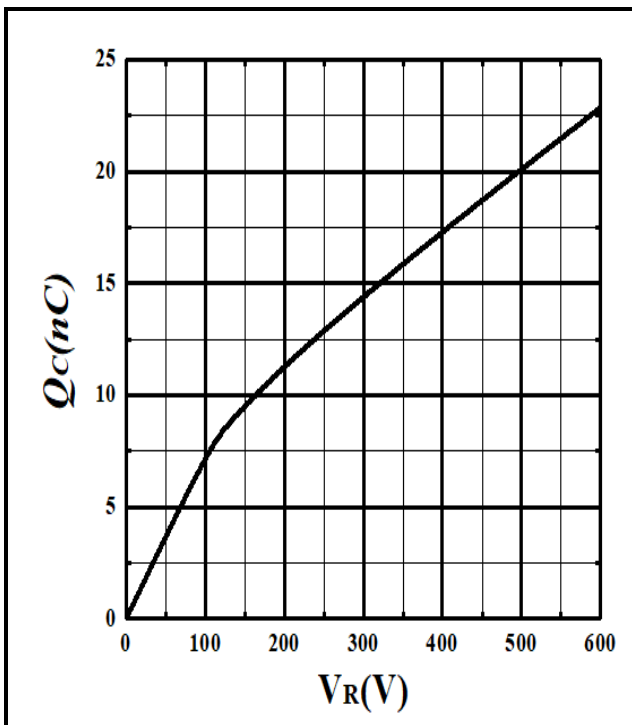


Figure 7. Total capacitance charge vs. reverse voltage

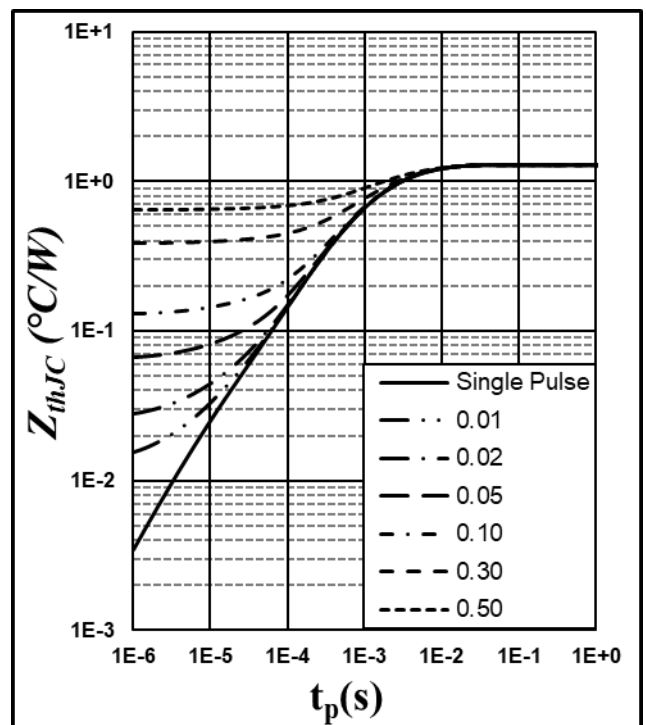
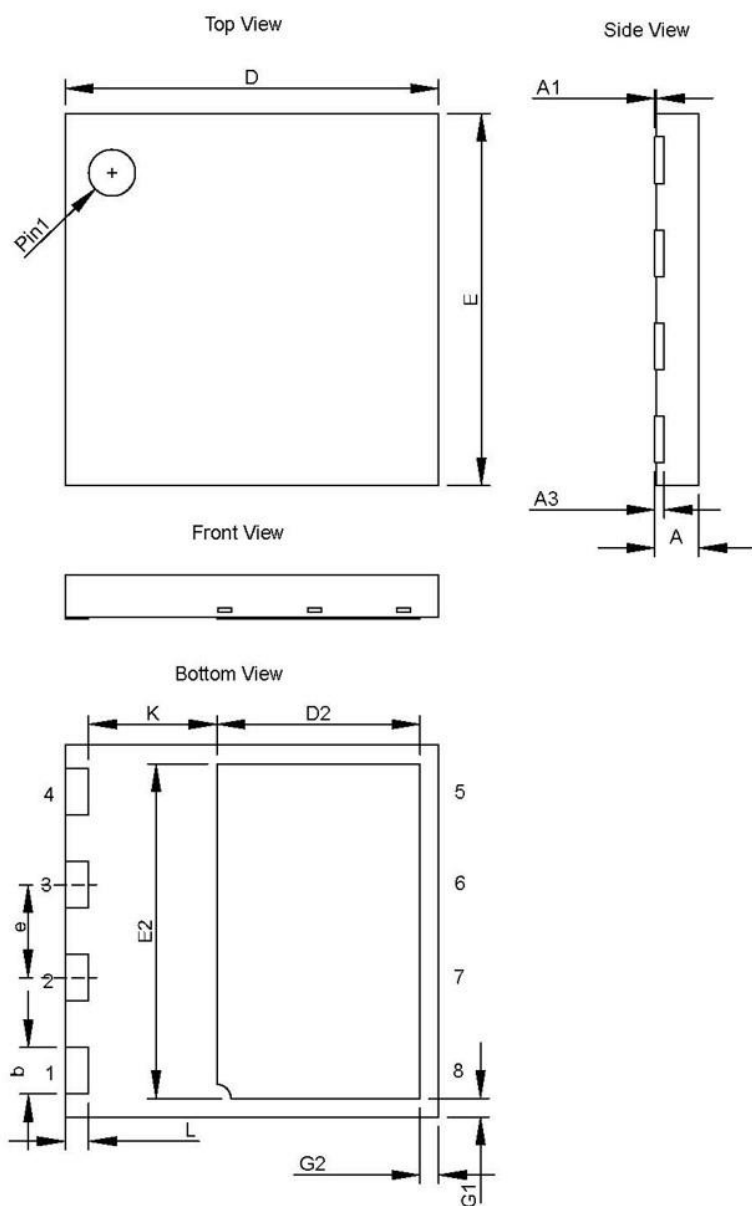


Figure 8. Transient Thermal Impedance
Junction Case

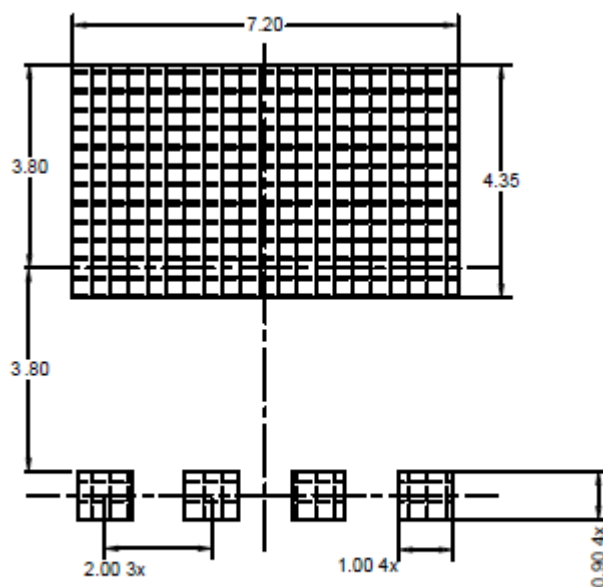
Package Information



Dimension unit: [mm]			
Symbol	Min	Nom	Max
A	0.80	0.90	1.00
A1	0.00	0.02	0.05
A3	0.203 REF		
b	0.90	1.00	1.10
D	7.90	8.00	8.10
E	7.90	8.00	8.10
D2	4.25	4.35	4.45
E2	7.10	7.20	7.30
e	1.90	2.00	2.10
K	2.65	2.75	2.85
L	0.40	0.50	0.60
G1	0.30	0.40	0.50
G2	0.30	0.40	0.50

Recommended Solder Pad Layout

Note: All dimensions are in mm



DFN 8*8-4L

Ordering Information

Part number	SDS065J006S3-ISBRH
Package	DFN 8*8-4L
Unit quantity	3000 EA
Packing type	Tape & Reel

Important Notices – Read Carefully

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